



M74HC283

4-BIT BINARY FULL ADDER

- HIGH SPEED :
 $t_{PD} = 17\text{ns}$ (TYP.) at $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 4\text{mA}$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- FULL-CARRY LOOK-AHEAD ACROSS THE FOUR BITS
- PARTIAL LOOK-AHEAD WITH THE ECONOMY OF RIPPLE CARRY
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 283



ORDER CODES

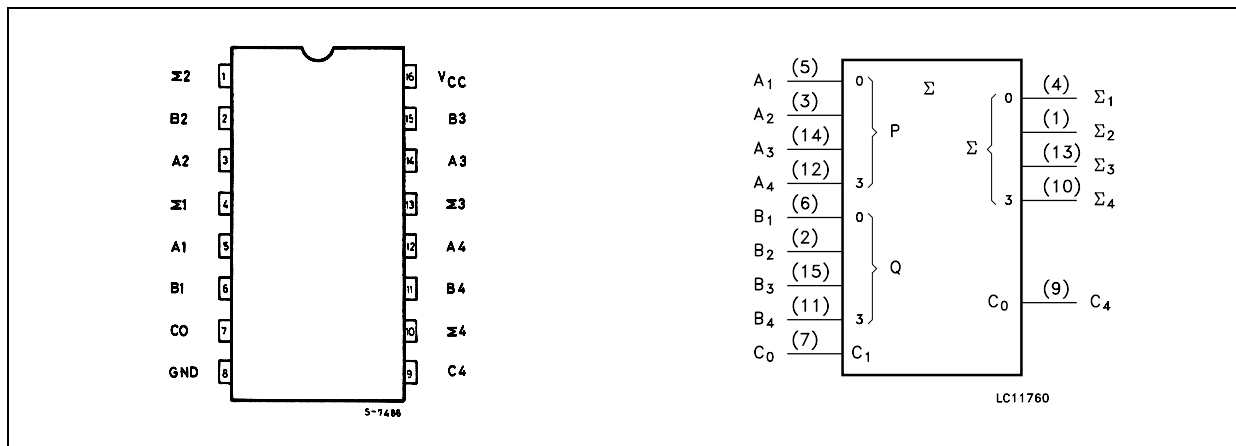
PACKAGE	TUBE	T & R
DIP	M74HC283B1R	
SOP	M74HC283M1R	M74HC283RM13TR
TSSOP		M74HC283TTR

DESCRIPTION

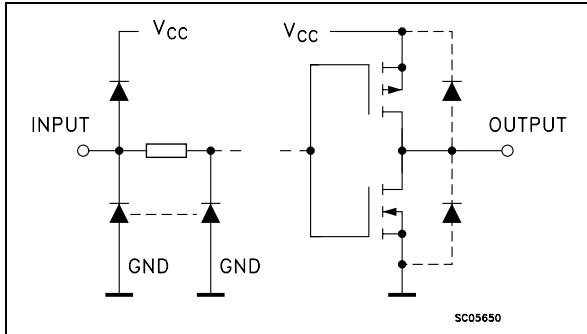
The M74HC283 is an high speed CMOS 4 BIT BINARY FULL ADDER fabricated with silicon gate C²MOS technology.

Sum (Σ) outputs are provided for each bit and a resultant carry (C_4) is obtained from the fourth bit. This adder features full internal look ahead across all four bits. A 4 x n binary adder is easily built up by cascading without any additional logic. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



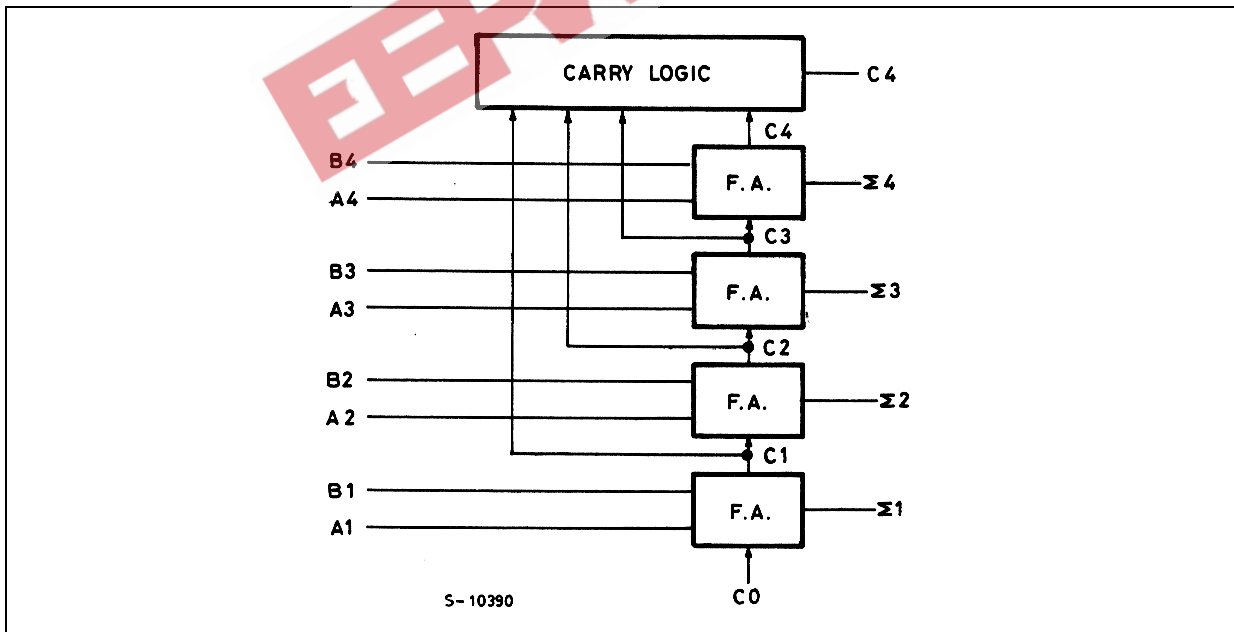
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
4, 1, 13, 10	$\Sigma 1$ to $\Sigma 4$	Sum Outputs
5, 3, 14, 12	A1 to A4	A Operand Inputs
6, 2, 15, 11	B1 to B4	B Operand Inputs
7	C0	Carry Input
9	C4	Carry Output
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

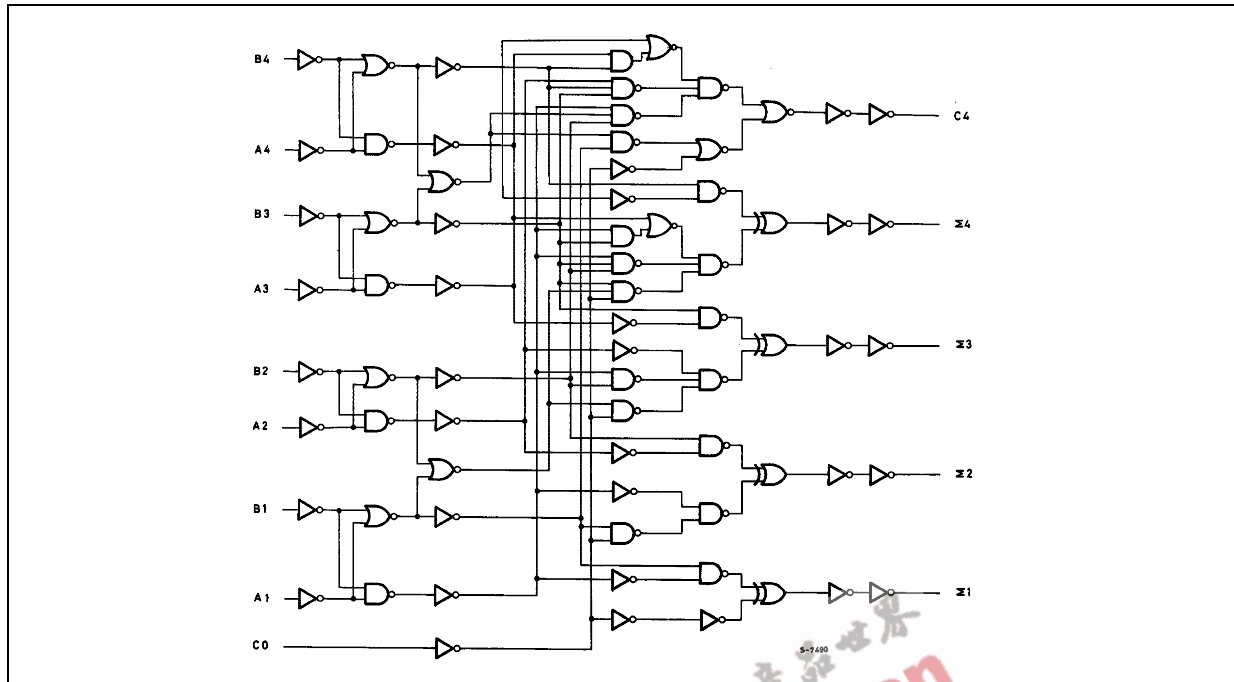
TRUTH TABLE

INPUTS			OUTPUTS	
Bn	An	Cn - 1	Σn	Cn
L	L	L	L	L
L	L	H	H	L
L	H	L	H	L
L	H	H	L	H
H	L	L	H	L
H	L	H	L	H
H	H	L	L	H
H	H	H	H	H

BLOCK DIAGRAM



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500(*)	mW
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$
T_L	Lead Temperature (10 sec)	300	$^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 $^{\circ}C$; derate to 300mW by 10mW/ $^{\circ}C$ from 65 $^{\circ}C$ to 85 $^{\circ}C$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature	-55 to 125	$^{\circ}C$	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V _{OH}	High Level Output Voltage	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output Voltage	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1		±1	μA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	μA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6ns)

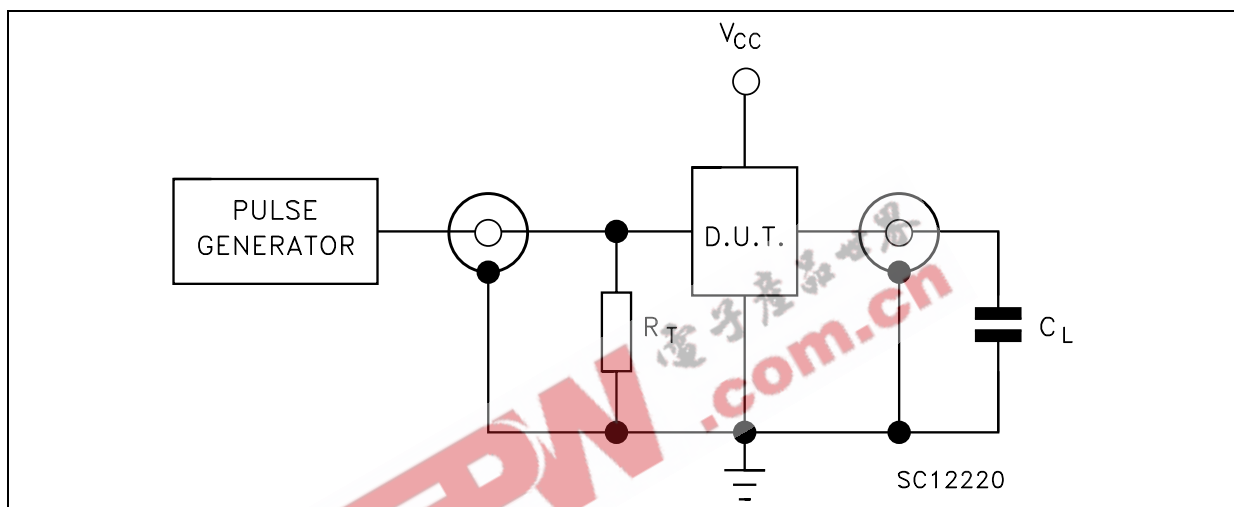
Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay Time (A _n , B _n - Σ _n)	2.0			95	210		265		315	ns
		4.5			27	42		53		63	
		6.0			22	36		45		54	
t _{PLH} t _{PHL}	Propagation Delay Time (A _n , B _n - C ₄)	2.0			80	195		245		295	ns
		4.5			25	39		49		59	
		6.0			20	33		42		50	
t _{PLH} t _{PHL}	Propagation Delay Time (C ₀ - Σ _n)	2.0			60	150		190		225	ns
		4.5			20	30		38		45	
		6.0			17	26		32		38	
t _{PLH} t _{PHL}	Propagation Delay Time (C ₀ - C ₄)	2.0			60	150		190		225	ns
		4.5			20	30		38		45	
		6.0			17	26		32		38	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			126						pF

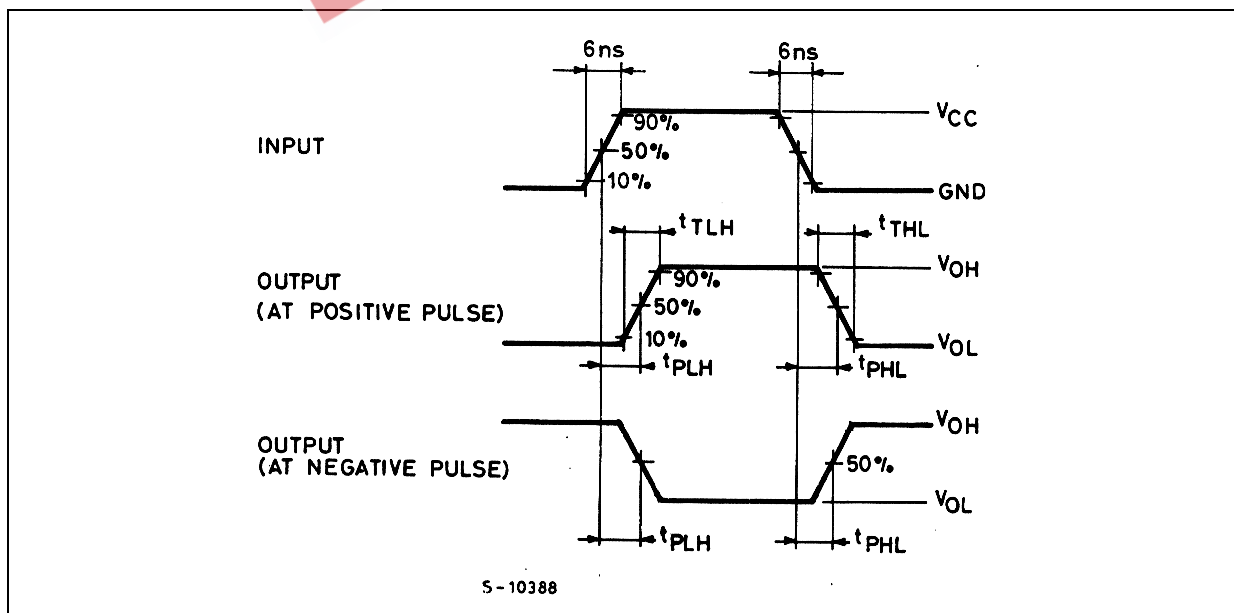
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT



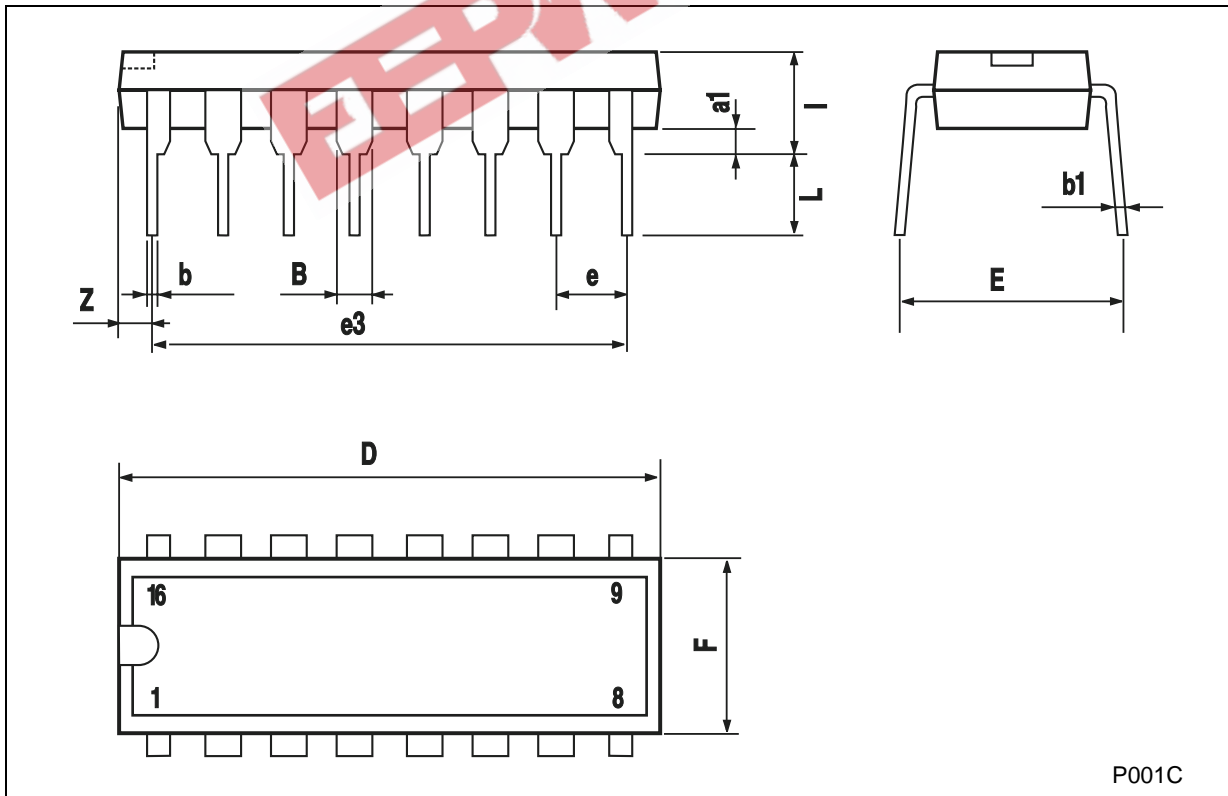
C_L = 50pF or equivalent (includes jig and probe capacitance)
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



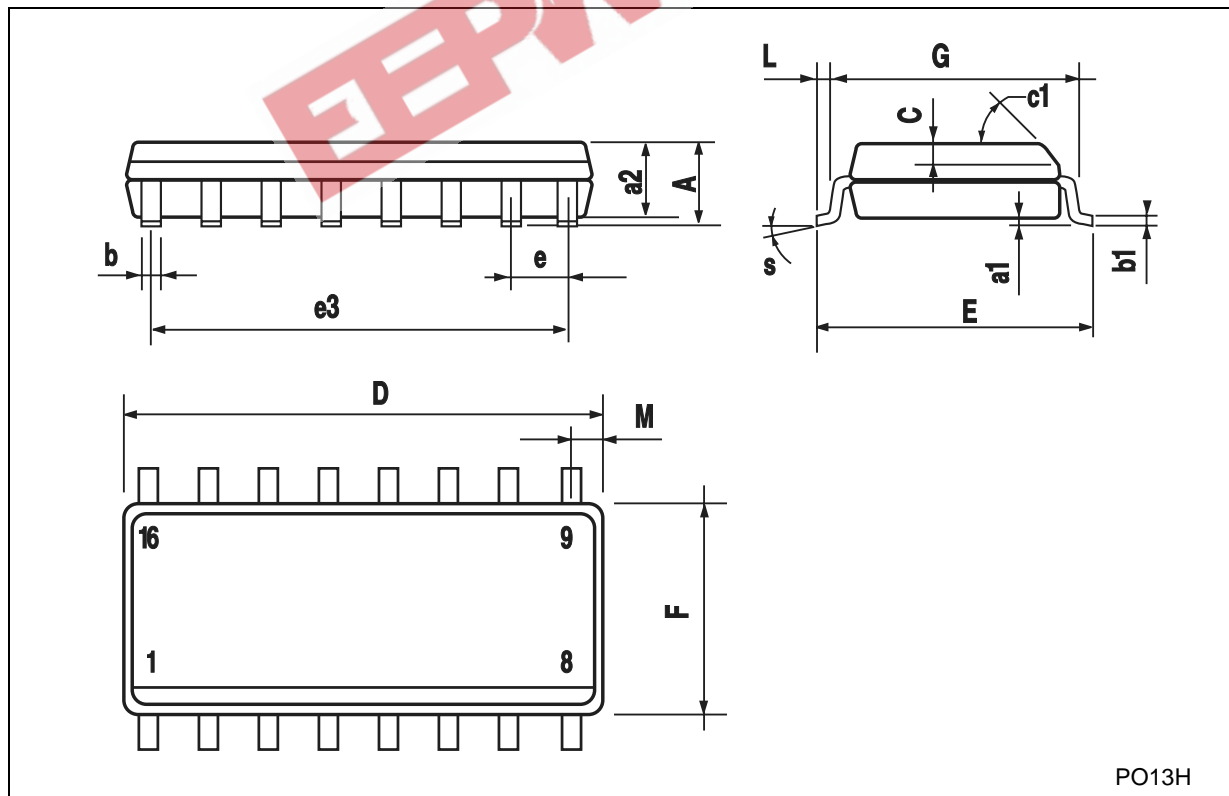
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



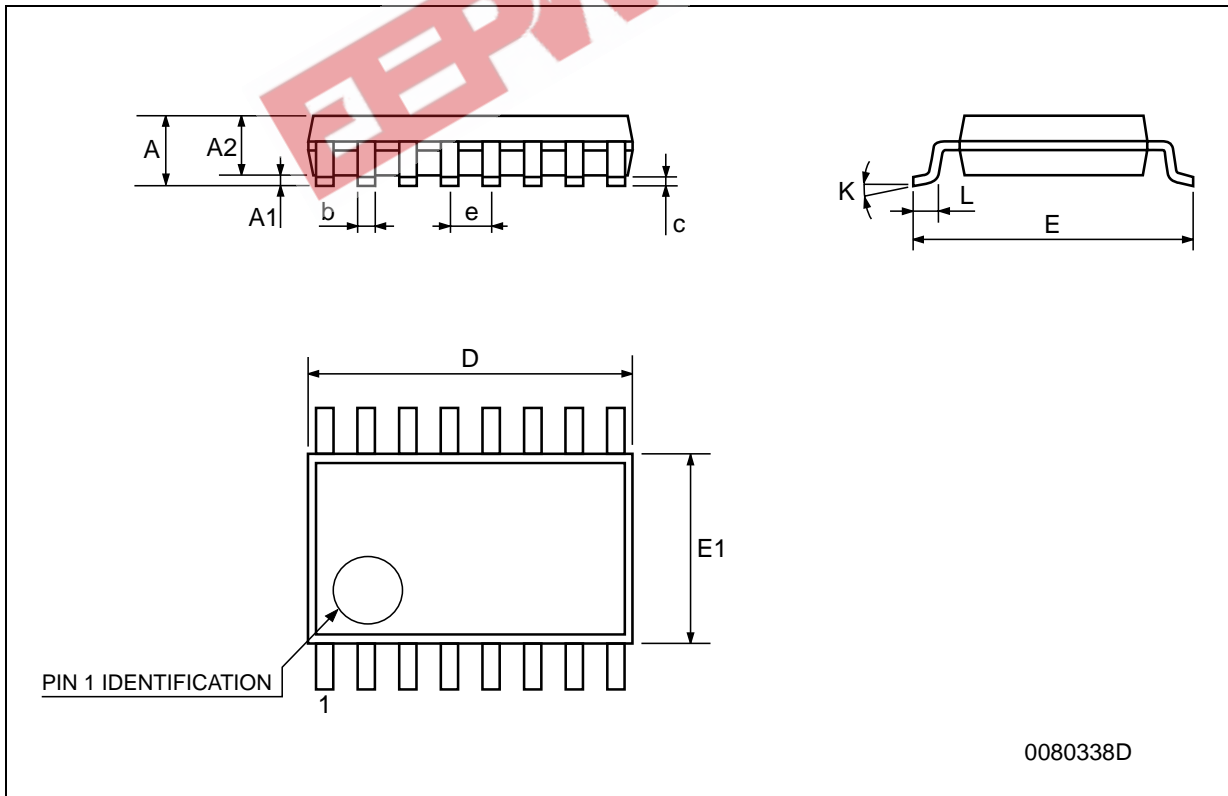
SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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